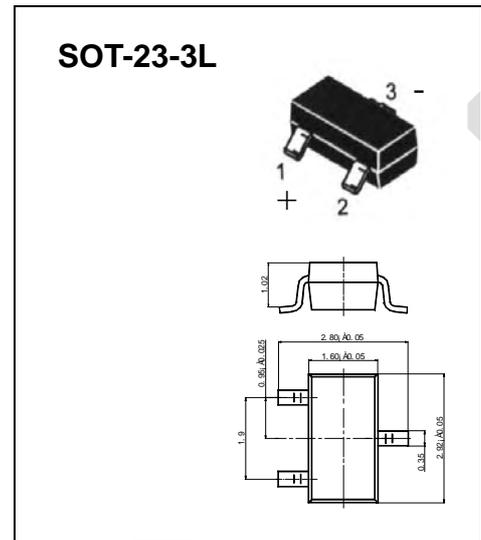


## RB421D Schottky barrier Diodes

### FEATURES

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

Marking: D3C



### Maximum Ratings and Electrical Characteristics, Single Diode @T<sub>A</sub>=25°C

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V <sub>RM</sub>	40	V
DC reverse voltage	V <sub>R</sub>	40	V
Mean rectifying current	I <sub>O</sub>	100	mA
Peak forward surge current	I <sub>FSM</sub>	1	A
Junction temperature	T <sub>j</sub>	125	°C
Storage temperature	T <sub>stg</sub>	-40~+125	°C

### Electrical Ratings @T<sub>A</sub>=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V <sub>F1</sub>			0.55	V	I <sub>F</sub> =100mA
	V <sub>F2</sub>			0.34	V	I <sub>F</sub> =10mA
Reverse current	I <sub>R</sub>			30	μA	V <sub>R</sub> =10V
Capacitance between terminals	C <sub>T</sub>		6		pF	V <sub>R</sub> =10V, f=1MHZ